

2SK3560

Silicon N-channel power MOSFET

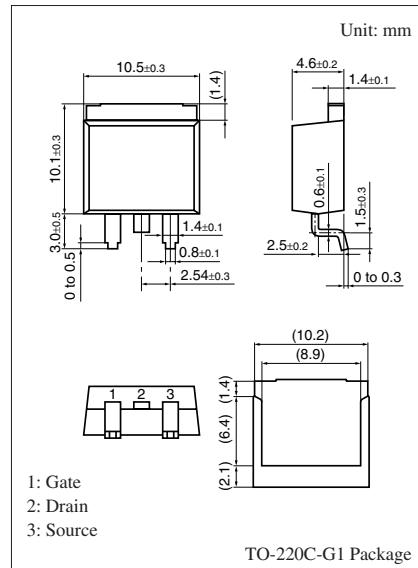
For PDP/For high-speed switching

■ Features

- Low on-resistance, low Q_g
- High avalanche resistance

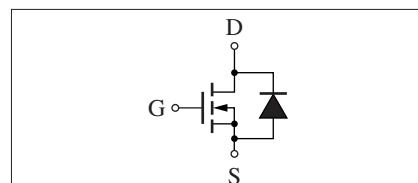
■ Absolute Maximum Ratings $T_C = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Drain-source surrender voltage	V_{DSS}	230	V
Gate-source surrender voltage	V_{GSS}	± 30	V
Drain current	I_D	30	A
Peak drain current	I_{DP}	120	A
Power dissipation $T_a = 25^\circ\text{C}$	P_D	50	W
		3	
Channel temperature	T_{ch}	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$



TO-220C-G1 Package

Internal Connection



■ Electrical Characteristics $T_C = 25^\circ\text{C} \pm 3^\circ\text{C}$

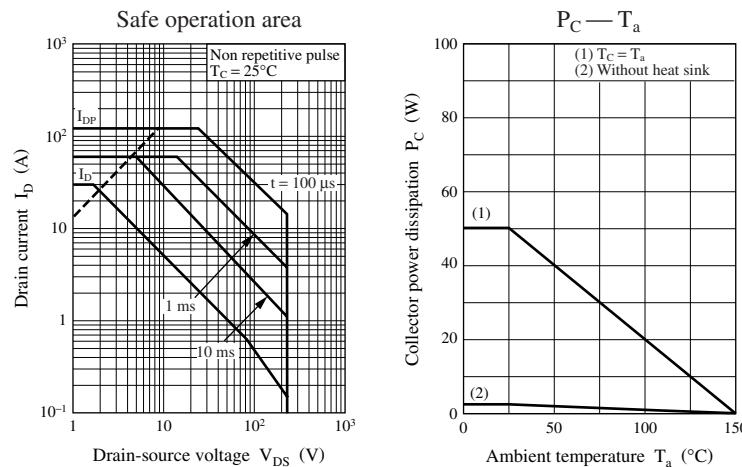
Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Gate-drain surrender voltage	V_{DSS}	$I_D = 1 \text{ mA}, V_{GS} = 0$	230			V
Diode forward voltage	V_{DSF}	$I_{DR} = 30 \text{ A}, V_{GS} = 0$			-1.5	V
Gate threshold voltage	V_{th}	$V_{DS} = 25 \text{ V}, I_D = 1 \text{ mA}$	2	4	4	V
Drain-source cutoff current	I_{DSS}	$V_{DS} = 184 \text{ V}, V_{GS} = 0$			100	μA
Gate-source cutoff current	I_{GSS}	$V_{GS} = \pm 30 \text{ V}, V_{DS} = 0$			± 1	μA
Drain-source on resistance	$R_{DS(on)}$	$V_{GS} = 10 \text{ V}, I_D = 15 \text{ A}$		55	74	$\text{m}\Omega$
Forward transfer admittance	$ Y_{fs} $	$V_{DS} = 25 \text{ V}, I_D = 15 \text{ A}$	8	19		S
Short-circuit forward transfer capacitance (Common-source)	C_{iss}	$V_{DS} = 25 \text{ V}, V_{GS} = 0, f = 1 \text{ MHz}$		2330		pF
Short-circuit output capacitance (Common-source)	C_{oss}			356		pF
Reverse transfer capacitance (Common-source)	C_{rss}			44		pF
Turn-on delay time	$t_{d(on)}$	$V_{DD} \approx 100 \text{ V}, I_D = 15 \text{ A}$ $R_L \approx 6.7 \Omega, V_{GS} = 10 \text{ V}$		39		ns
Rise time	t_r			37		ns
Turn-off delay time	$t_{d(off)}$			221		ns
Fall time	t_f			46		ns
Reverse recovery time	t_{rr}	$L = 230 \mu\text{H}, V_{DD} = 100 \text{ V}$		164		ns
Reverse recovery charge	Q_{rr}		$I_{DR} = 15 \text{ A}, di/dt = 100 \text{ A}/\mu\text{s}$	853		nC

Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

■ Electrical Characteristics (Continued) $T_C = 25^\circ\text{C} \pm 3^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Total gate charge	Q_g	$V_{DD} = 100 \text{ V}, I_D = 25 \text{ A}$ $V_{GS} = 10 \text{ V}$		51.2		nC
Gate-source charge	Q_{gs}			8.2		nC
Gate-drain charge	Q_{gd}			19.4		nC
Channel-case heat resistance	$R_{th(\text{ch-c})}$				2.5	°C/W
Channel-atmosphere heat resistance	$R_{th(\text{ch-a})}$				89.2	°C/W

Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.



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